

# ABSTRACT OF THE DISCLOSURE

When the Cu-containing aluminum film is dry-etched with etching gas containing chlorine gas, the gas stay time  $\tau$  of the etching gas staying in the chamber, which is expressed by

- 5  $P \cdot V/Q$ , where  $P$  being the chamber pressure (unit: Pa),  $V$  the chamber volume (unit: L) and  $Q$  the total flow of etching gas (unit: Pa  $\cdot$  L/sec), is from 0.15 seconds to 0.30 seconds inclusive.

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